

GE85T08

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

BVDSS	80V
RDS(ON)	13mΩ
ID	75A

Description

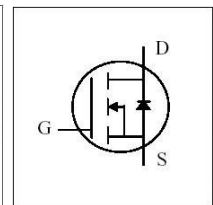
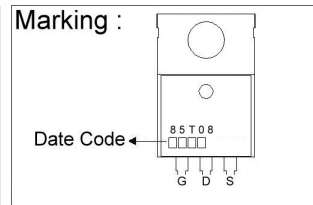
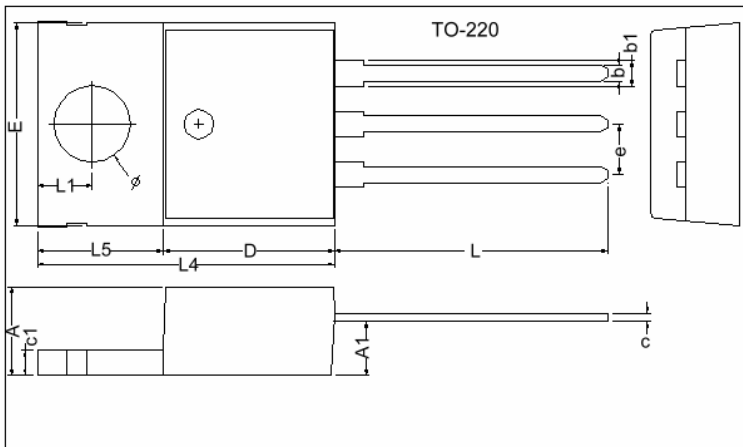
The GE85T08 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The through-hole version (TO-220) is available for low-profile applications and suited for low voltage applications such as DC/DC converters.

Features

- *Simple Drive Requirement
- *Lower On-resistance
- *Fast Switching

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	Ø	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=25^{\circ}C$	75	A
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=100^{\circ}C$	48	A
Pulsed Drain Current ¹	I_{DM}	260	A
Total Power Dissipation	$P_D @T_C=25^{\circ}C$	138	W
Linear Derating Factor		1.11	W/°C
Single Pulse Avalanche Energy ³	E_{AS}	450	mJ
Avalanche Current	I_{AR}	30	A
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	R_{thj-c}	0.9	°C/W
Thermal Resistance Junction-ambient Max.	R_{thj-a}	62	°C/W

Electrical Characteristics(T_j = 25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	80	-	-	V	$V_{GS}=0, I_D=1mA$
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	0.09	-	V/°C	Reference to 25°C, $I_D=1mA$
Gate Threshold Voltage	$V_{GS(th)}$	1.0	-	3.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Forward Transconductance	g_{fs}	-	70	-	S	$V_{DS}=10V, I_D=45A$
Gate-Source Leakage Current	I_{GSS}	-	-	±100	nA	$V_{GS}= \pm 20V$
Drain-Source Leakage Current(T _j =25°C)	I_{DSS}	-	-	10	uA	$V_{DS}=80V, V_{GS}=0$
Drain-Source Leakage Current(T _j =150°C)		-	-	100	uA	$V_{DS}=64V, V_{GS}=0$
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	-	-	13	mΩ	$V_{GS}=10V, I_D=45A$
		-	-	18		$V_{GS}=4.5V, I_D=25A$
Total Gate Charge ²	Q_g	-	63	100	nC	$I_D=45A$ $V_{DS}=64V$ $V_{GS}=4.5V$
Gate-Source Charge	Q_{gs}	-	23	-		
Gate-Drain ("Miller") Charge	Q_{gd}	-	38	-		
Turn-on Delay Time ²	$T_{d(on)}$	-	30	-	ns	$V_{DS}=40V$ $I_D=45A$ $V_{GS}=10V$ $R_G=10\Omega$ $R_D=0.89\Omega$
Rise Time	T_r	-	100	-		
Turn-off Delay Time	$T_{d(off)}$	-	144	-		
Fall Time	T_f	-	173	-		
Input Capacitance	C_{iss}	-	6300	10080	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHz$
Output Capacitance	C_{oss}	-	670	-		
Reverse Transfer Capacitance	C_{riss}	-	350	-		
Gate Resistance	R_g	-	1.1	1.7		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V_{SD}	-	-	1.3	V	$I_S=45A, V_{GS}=0V$
Reverse Recovery Time ²	T_{rr}	-	47	-	ns	$I_S=20A, V_{GS}=0V$ $di/dt=100A/\mu s$
Reverse Recovery Charge	Q_{rr}	-	86	-	nC	

Notes: 1. Pulse width limited by safe operating area.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

3. Staring T_j=25°C, V_{DD}=30V, L=1mH, R_G=25Ω, I_{AS}=30A.

Characteristics Curve

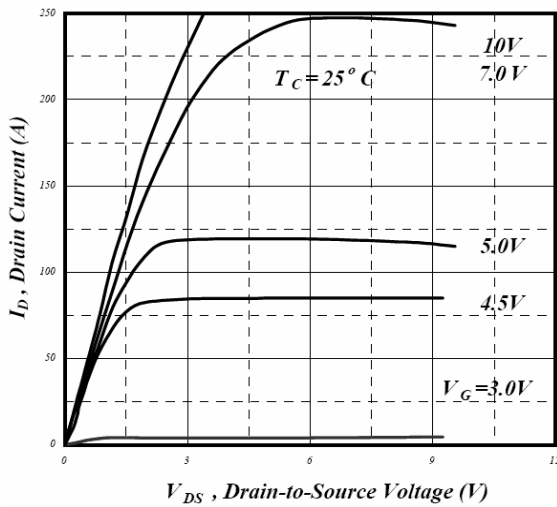


Fig 1. Typical Output Characteristics

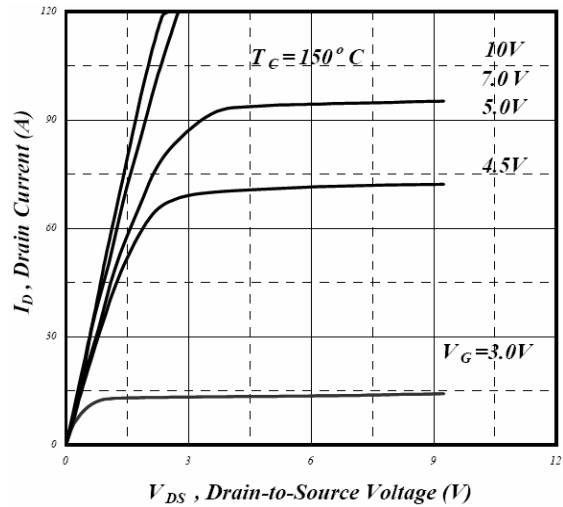


Fig 2. Typical Output Characteristics

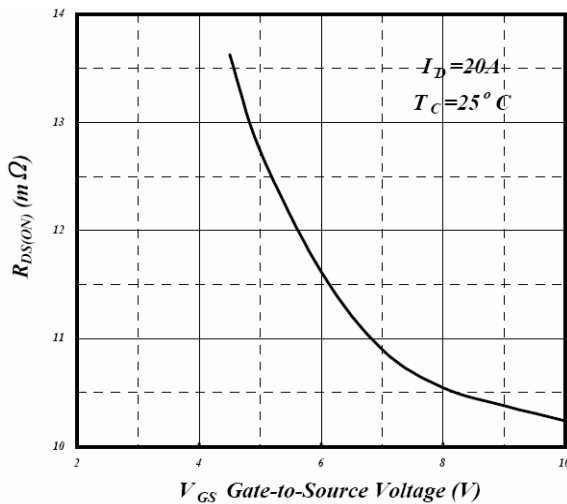


Fig 3. On-Resistance v.s. Gate Voltage

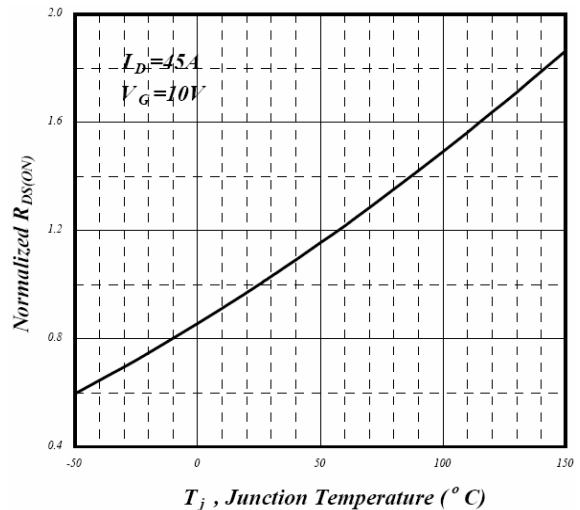


Fig 4. Normalized On-Resistance v.s. Junction Temperature

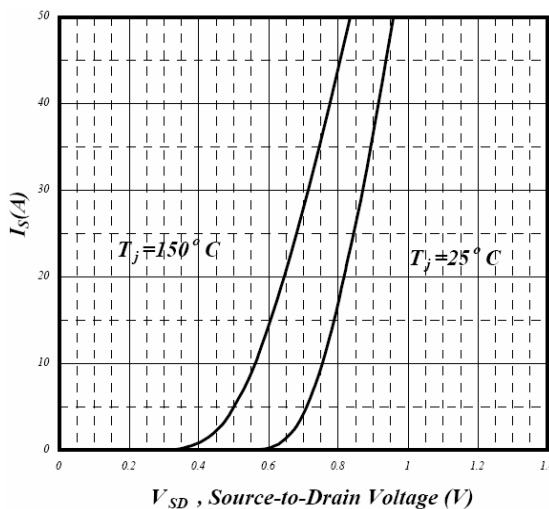


Fig 5. Forward Characteristics of Reverse Diode

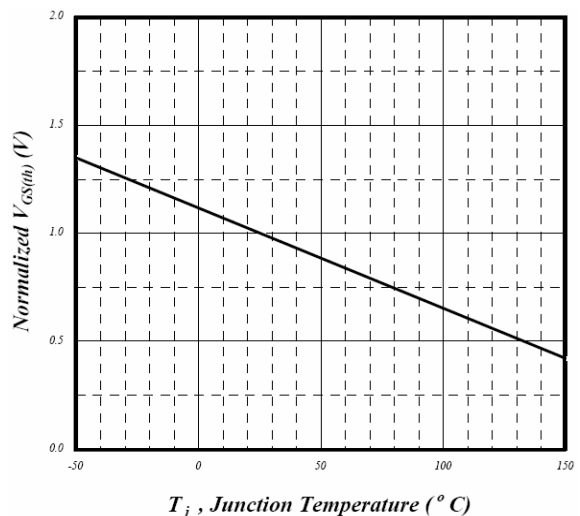


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

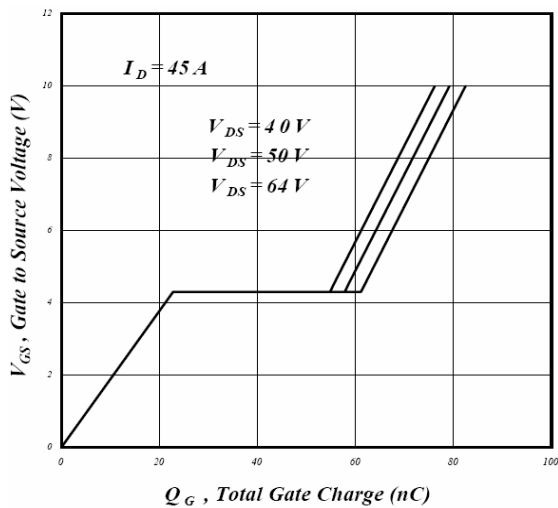


Fig 7. Gate Charge Characteristics

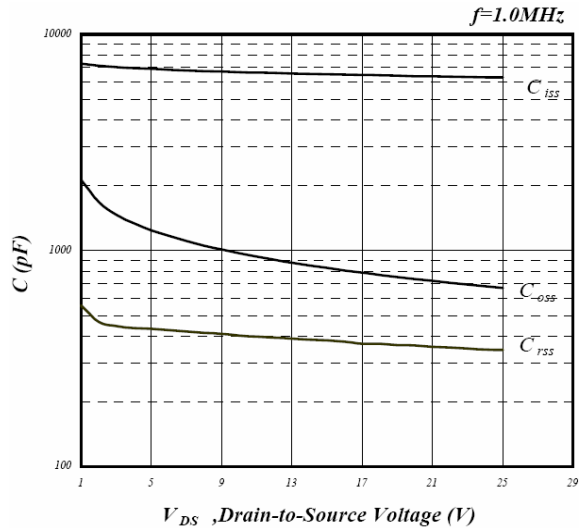


Fig 8. Typical Capacitance Characteristics

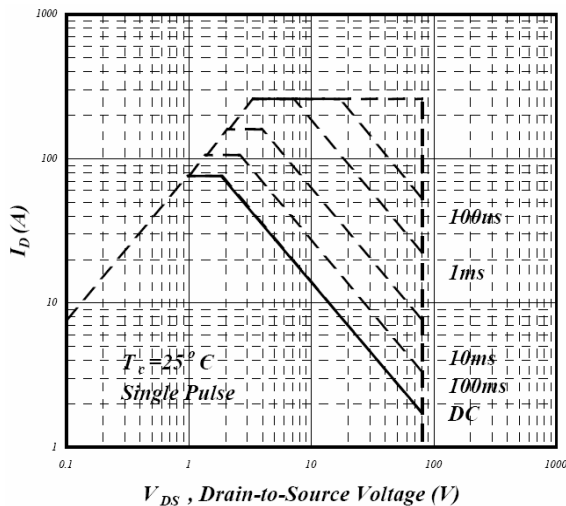


Fig 9. Maximum Safe Operating Area

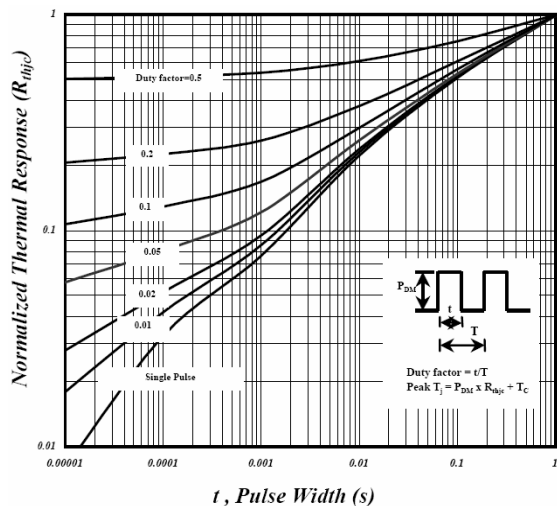


Fig 10. Effective Transient Thermal Impedance

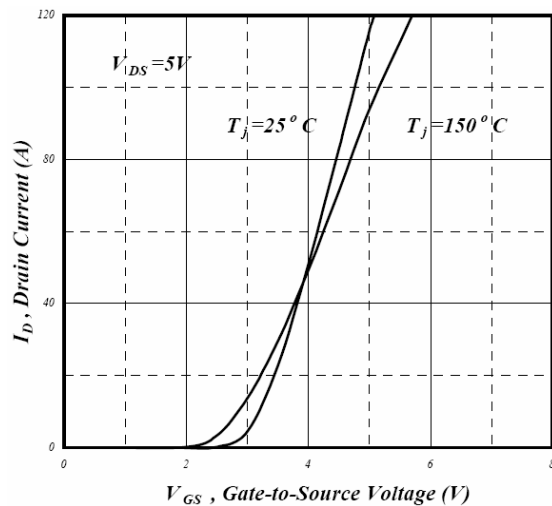


Fig 11. Transfer Characteristics

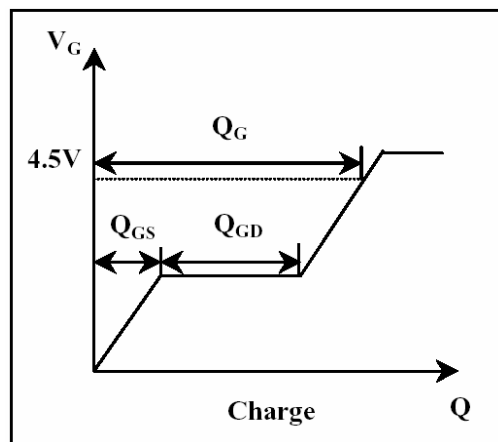


Fig 12. Gate Charge Waveform

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